

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-5,877,558	03-1999	Nakamura et al.	257/749
	В	US-			
	С	US-			
	D	US-			
	E	US-			
	F	US-		·	
	G	US-			
-	Н	US-			
	_	US-			
	J	US-			
	К	US-			
	L	US-			·
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP 9-167857	06-1997	Japan	Fujimoto et al.	H01L 33/00
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)				
	υ	Stringfellow et al., "High Brightness Light Emitting Diodes," Semiconductors and Semimetals, 1997, Vol. 48, pages 195-199.				
-	٧	Schnitzer et al., "Ultrahigh spontaneous emission quantum efficiency, 99.7% internally and 72% externally, from AlGaAs/GaAs/AlGaAs double heterostructures," Appl. Phys. Lett. 62 (2), 11 January 1993, pp. 131-133.				
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.